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(54) MANUFACTURE OF SEMICONDUCTOR DEVICE

(57) Abstract:

PROBLEM TO BE SOLVED: To enable sealing of post metals with a sufficient film thickness therearound and suppression of remaining voids in sealing resin, advantageously from the view point of cost.

SOLUTION: In this method a semiconductor device is manufactured with the use of a wafer Wf, having a circuit element and electrode pads 20 for conduction with the circuit element formed thereon and having a plurality of regions thereon. In this case, the method include the steps of forming post metals 4 to be conducted with the pads 20, forming a resin layer 40A to bury the post metals 4, and partitioning the wafer Wf by regions for individual semiconductor devices. The step of forming the resin layer 40A is carried out through printing method under vacuum by burying the post metals 4 with viscous resin 40a therearound and causing the resin to set.



